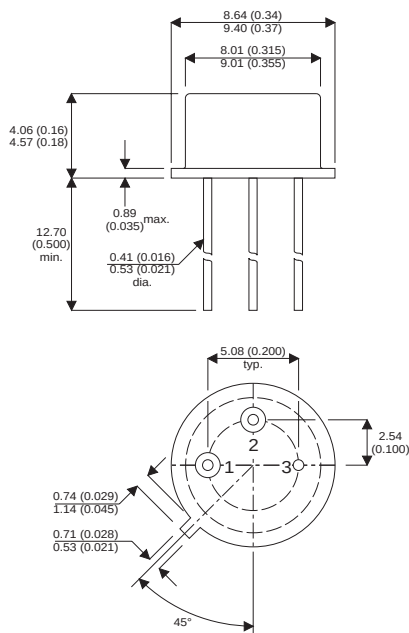


MECHANICAL DATA

Dimensions in mm (inches)



TO39 – Package (TO-205AF)

Underside View

Pin 1 – Source Pin 2 – Gate Pin 3 – Drain

N-CHANNEL ENHANCEMENT MODE POWER MOSFET

BV_{DSS} 500V

$I_{D(cont)}$ 2.5

$R_{DS(on)}$ 1.5Ω

FEATURES

- AVALANCHE ENERGY RATED
- HERMETICALLY SEALED
- DYNAMIC dv/dt RATING
- SIMPLE DRIVE REQUIREMENTS

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

V_{GS}	Gate – Source Voltage	±20V
I_D	Continuous Drain Current ($V_{GS} = 10V$, $T_{case} = 25^{\circ}C$)	2.5A
I_D	Continuous Drain Current ($V_{GS} = 10V$, $T_{case} = 100^{\circ}C$)	1.5A
I_{DM}	Pulsed Drain Current ¹	11A
P_D	Power Dissipation @ $T_{case} = 25^{\circ}C$	25W
	Linear Derating Factor	0.2W/ $^{\circ}C$
E_{AS}	Single Pulse Avalanche Energy ²	0.35mJ
dv/dt	Peak Diode Recovery ³	3.5V/ns
T_J , T_{stg}	Operating and Storage Temperature Range	-55 to +150 $^{\circ}C$
$R_{\theta JC}$	Thermal Resistance Junction to Case	5.0 $^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	175 $^{\circ}C/W$

Notes

- 1) Pulse Test: Pulse Width $\leq 300\mu s$, $\delta \leq 2\%$
- 2) @ $V_{DD} = 50V$, Peak $I_L = 2.5A$, Starting $T_J = 25^{\circ}C$
- 3) @ $I_{SD} \leq 2.5A$, $di/dt \leq 75A/\mu s$, $V_{DD} \leq BV_{DSS}$, $T_J \leq 150^{\circ}C$, SUGGESTED $R_G = 7.5\Omega$

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Issue: 1

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter		Test Conditions		Min.	Typ.	Max.	Unit
STATIC ELECTRICAL RATINGS							
BV _{DSS}	Drain – Source Breakdown Voltage	V _{GS} = 0	I _D = 1mA	500			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Temperature Coefficient of Breakdown Voltage	Reference to 25°C I _D = 1mA			0.43		V/°C
R _{DS(on)}	Static Drain – Source On–State Resistance	V _{GS} = 10V	I _D = 1.5A			1.5	Ω
		V _{GS} = 10V	I _D = 2.5A			1.725	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS}	I _D = 250μA	2		4	V
g _{fs}	Forward Transconductance	V _{DS} > 15V	I _{DS} = 1.5A	1.5			S(Ω)
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} = 0	V _{DS} = 0.8BV _{DSS}			25	μA
			T _J = 125°C			250	
I _{GSS}	Forward Gate – Source Leakage	V _{GS} = 20V				100	nA
I _{GSS}	Reverse Gate – Source Leakage	V _{GS} = –20V				–100	
DYNAMIC CHARACTERISTICS							
C _{iss}	Input Capacitance	V _{GS} = 0			610		pF
C _{oss}	Output Capacitance	V _{DS} = 25V			135		
C _{rss}	Reverse Transfer Capacitance	f = 1MHz			65		
Q _g	Total Gate Charge	V _{GS} = 10V		19.8		29.5	nC
Q _{gs}	Gate – Source Charge	V _{DS} = 0.5BV _{DS}		2.2		4.6	
Q _{gd}	Gate – Drain (“Miller”) Charge	I _D = 2.5A		5.5		19.7	
t _{d(on)}	Turn–On Delay Time	I _D =2.5A				30	ns
t _r	Rise Time	V _{DS} = 0.5BV _{DS}				30	
t _{d(off)}	Turn–Off Delay Time	R _G = 7.5Ω				55	
t _f	Fall Time					30	
SOURCE – DRAIN DIODE CHARACTERISTICS							
I _S	Continuous Source Current					2.5	A
I _{SM}	Pulse Source Current ²	I _S = 2.5A	V _{GS} = 0			11	
V _{SD}	Diode Forward Voltage	I _F = 1.5A	T _J = 25°C			1.4	V
t _{rr}	Reverse Recovery Time	I _F = 2.5A	T _J = 25°C			900	ns
Q _{rr}	Reverse Recovery Charge	d _i / d _t ≤ 100A/μs V _{DD} ≤ 50V				7.0	μC
t _{on}	Forward Turn–On Time				Negligible		

Notes

- 1) Pulse Test: Pulse Width $\leq 300\mu\text{s}$, $\delta \leq 2\%$
- 2) Repetitive Rating – Pulse width limited by maximum junction temperature.